

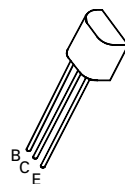
# PNP SILICON PLANAR MEDIUM POWER HIGH VOLTAGE TRANSISTOR

## FXT757

ISSUE 1 – FEB 94

### FEATURES

- \* 300 Volt  $V_{CE0}$
- \* 0.5 Amp continuous current
- \*  $P_{tot} = 1$  Watt



E-Line  
TO92 Compatible

REFER TO ZTX757 FOR GRAPHS

### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	-300	V
Collector-Emitter Voltage	$V_{CEO}$	-300	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Peak Pulse Current	$I_{CM}$	-1	A
Continuous Collector Current	$I_C$	-0.5	A
Power Dissipation at $T_{amb} = 25^\circ\text{C}$	$P_{tot}$	1	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200	$^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ ).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-300			V	$I_C = -100\mu\text{A}$ , $I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-300			V	$I_C = -10\text{mA}$ , $I_B = 0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu\text{A}$ , $I_C = 0$
Collector Cut-Off Current	$I_{CBO}$			-100	nA	$V_{CB} = -200\text{V}$ , $I_E = 0$
Emitter Cut-Off Current	$I_{EBO}$			-100	nA	$V_{EB} = -3\text{V}$ , $I_C = 0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.5	V	$I_C = -100\text{mA}$ , $I_B = -10\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1.0	V	$I_C = -100\text{mA}$ , $I_B = -10\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			-1.0	V	$I_C = -100\text{mA}$ , $V_{CE} = -5\text{V}^*$
Static Forward Current Transfer Ratio	$h_{FE}$	40 50				$I_C = -10\text{mA}$ , $V_{CE} = -5\text{V}^*$ $I_C = -100\text{mA}$ , $V_{CE} = -5\text{V}^*$
Transition Frequency	$f_T$	30			MHz	$I_C = -10\text{mA}$ , $V_{CE} = -20\text{V}$ $f = 20\text{MHz}$
Output Capacitance	$C_{obo}$			20	pF	$V_{CB} = -20\text{V}$ , $f = 1\text{MHz}$

\*Measured under pulsed conditions. Pulse width=300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$